

Description

The ASM33H is an uni-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The ASM33H complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

- 700W peak pulse power (8/20 μs)
- Protects one two uni-directional line(s)
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 40A (8/20 μs)
- RoHS Compliant

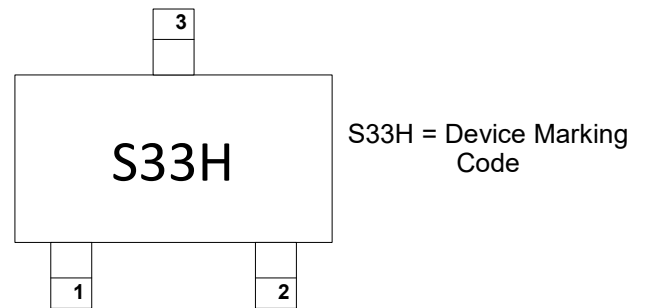
Mechanical Characteristics

- Package: SOT-23
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Peripherals
- Industrial Equipment
- Notebook Computers
- Portable Instrumentation
- Microprocessor Based Equipment
- Cell Phone Handsets and Accessories
- Personal Digital Assistants (PDAs) and Pagers

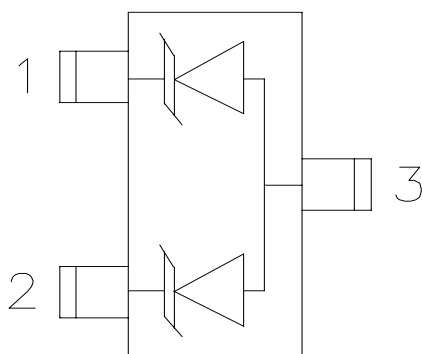
Marking Information



Ordering Information

Part Number	Packaging	Reel Size
ASM33H	3000/Tape & Reel	7 inch

Dimensions and Pin Configuration



SOT23

Circuit and Pin Schematic

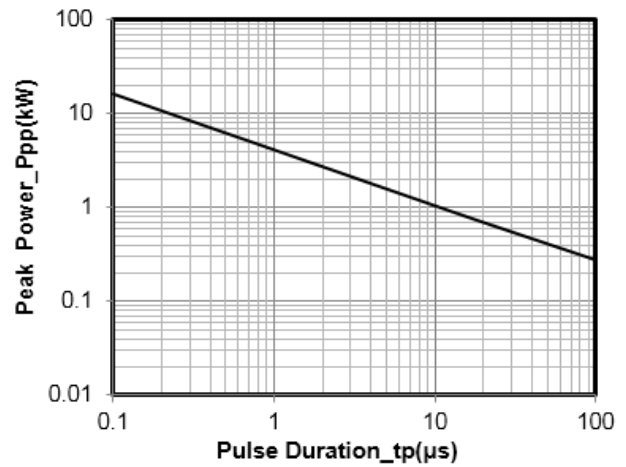
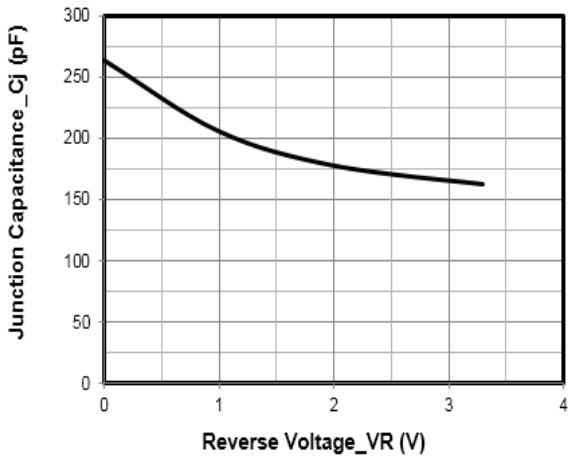
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	500	W
Peak Pulse Current (8/20 μs)	I _{PP}	40	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

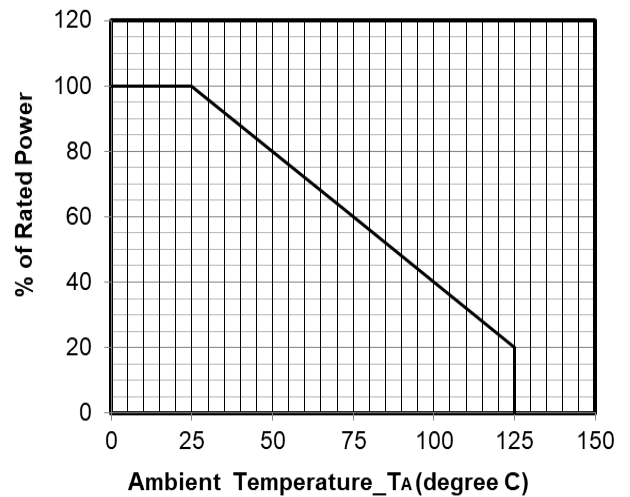
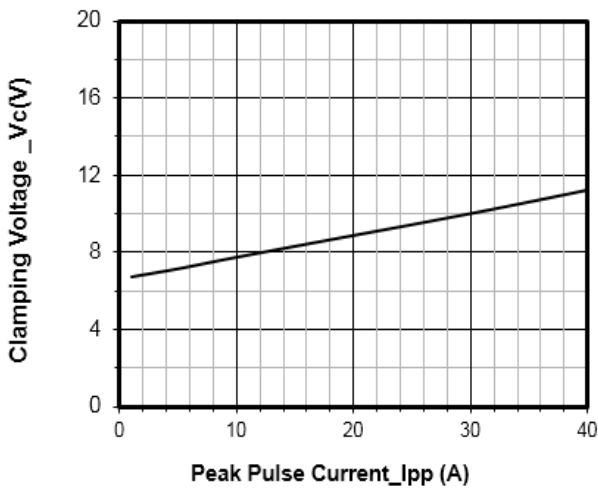
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			3.3	V	
Reverse Breakdown Voltage	V _{BR}	3.5			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 3.3V, any I/O pin to ground
Clamping Voltage	V _C			8	V	I _{PP} = 1A (8 x 20 μs pulse), any I/O pin to ground
Clamping Voltage	V _C			12.5	V	I _{PP} = 40A (8 x 20 μs pulse), any I/O pin to ground
Junction Capacitance	C _J		260		pF	V _R = 0V, f = 1MHz, any I/O pin to ground

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



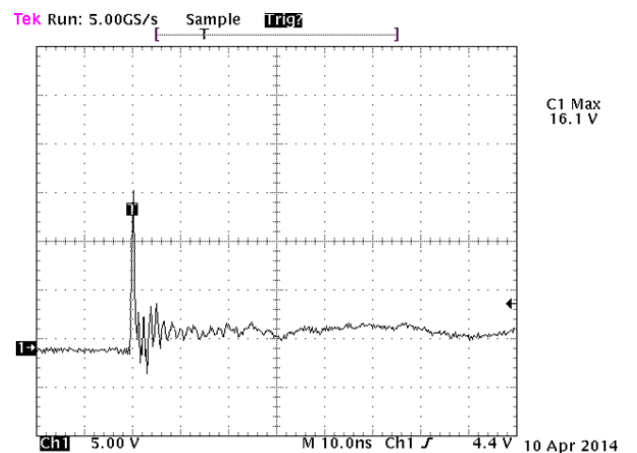
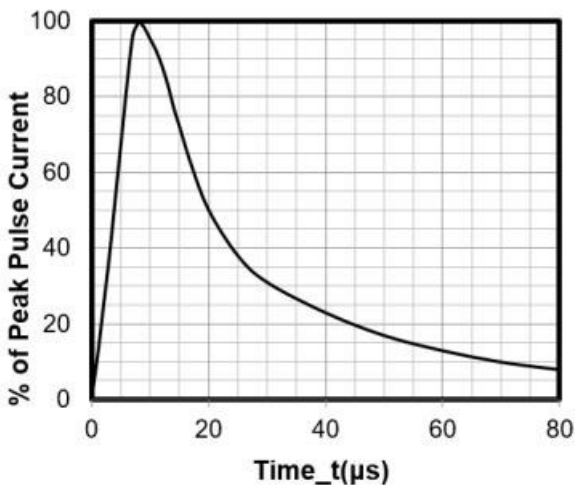
Junction Capacitance vs. Reverse Voltage

Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

Power Derating Curve

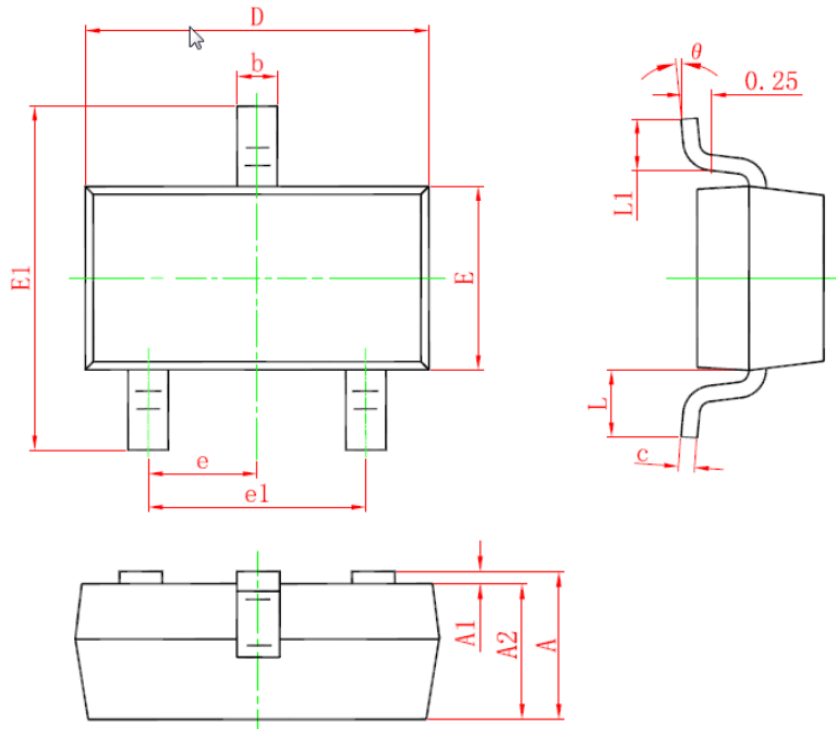


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

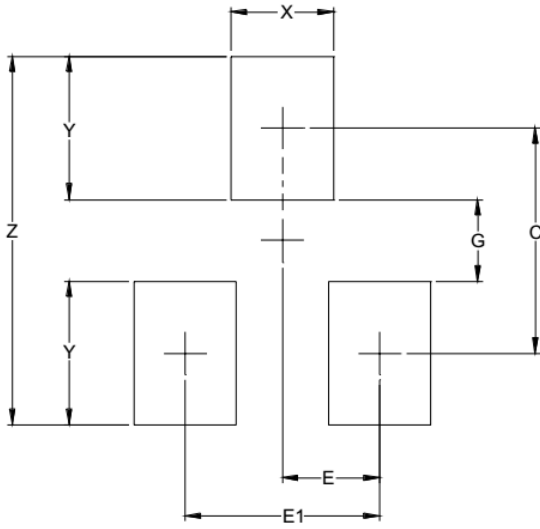
8 kV Contact per IEC61000-4-2

8 X 20μs Pulse Waveform

SOT-23 Package Outline Drawing


SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	--	1.15	0.035	--	0.045
A1	0.00	--	0.10	0.000	--	0.004
A2	0.90	--	1.05	0.035	--	0.041
b	0.30	--	0.50	0.012	--	0.020
c	0.08	--	0.15	0.003	--	0.006
D	2.80	--	3.00	0.110	--	0.118
E	1.20	--	1.40	0.047	--	0.055
E1	2.25	--	2.55	0.089		0.100
e	0.95TYP			0.037TYP		
e1	1.80	--	2.00	0.071	--	0.079
L	0.55REF			0.022REF		
L1	0.30	--	0.50	0.012	--	0.020
Θ	0°	--	8°	0°	--	8°

Suggested Land Pattern



SYM	DIMENSIONS	
	INCHES	MILLIMETERS
C	.087	2.20
E	.037	0.95
E1	.075	1.90
G	.031	0.80
X	.039	1.00
Y	.055	1.40
Z	.141	3.60

Contact Information

Applied Power Microelectronics Inc.

Website: <http://www.appliedpowermicro.com>

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606